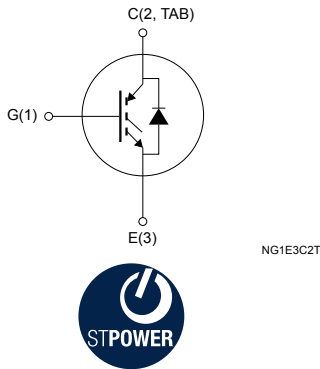
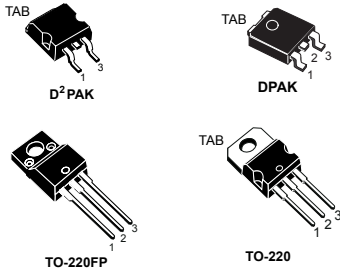


## 8 A, 600 V short-circuit rugged IGBT



### Features

- Lower on voltage drop ( $V_{CE(sat)}$ )
- Lower  $C_{res} / C_{ies}$  ratio (no cross-conduction susceptibility)
- Very soft ultra fast recovery antiparallel diode
- Short-circuit withstand time 10  $\mu$ s

### Applications

- High frequency motor controls
- SMPS and PFC in both hard switch and resonant topologies
- Motor drives

### Description

These devices are very fast IGBTs developed using advanced PowerMESH technology. This process guarantees an excellent trade-off between switching performance and low on-state behavior. These devices are well-suited for resonant or soft-switching applications.

#### Product status links

[STGB8NC60KD](#)

[STGD8NC60KD](#)

[STGF8NC60KD](#)

[STGP8NC60KD](#)

# 1 Electrical ratings

**Table 1. Absolute maximum ratings**

Symbol	Parameter	Value			Unit
		D <sup>2</sup> PAK, TO-220	DPAK	TO-220FP	
V <sub>CES</sub>	Collector-emitter voltage (V <sub>GE</sub> = 0 V)	600			V
I <sub>C</sub> <sup>(1)</sup>	Continuous collector current at T <sub>C</sub> = 25 °C	15		7	A
	Continuous collector current at T <sub>C</sub> = 100 °C	8		4	
I <sub>CL</sub> <sup>(2)</sup>	Turn-off latching current	30			A
I <sub>CP</sub> <sup>(3)</sup>	Pulsed collector current	30			A
V <sub>GE</sub>	Gate-emitter voltage	±20			V
I <sub>F</sub>	Diode RMS forward current at T <sub>C</sub> = 25 °C	7			A
I <sub>FSM</sub>	Surge non repetitive forward current t <sub>p</sub> = 10 ms sinusoidal	20			A
V <sub>ISO</sub>	Insulation withstand voltage (RMS) from all three leads to external heat sink (t = 1 s, T <sub>C</sub> = 25 °C)			2.5	kV
t <sub>scw</sub>	Short-circuit withstand time V <sub>CE</sub> = 0.5, V <sub>CES</sub> , T <sub>J</sub> = 125 °C, R <sub>G</sub> = 10 Ω, V <sub>GE</sub> = 12 V	10			μs
P <sub>TOT</sub>	Total power dissipation at T <sub>C</sub> = 25 °C	65	62	24	W
T <sub>stg</sub>	Storage temperature range	-55 to 150			°C
T <sub>J</sub>	Operating junction temperature range				°C

1. Calculated according to the iterative formula:  $I_C(T_C) = \frac{T_{J(max)} - T_C}{R_{thJC} \times V_{CE(sat)(max)}(T_{J(max)}, I_C(T_C))}$
2. V<sub>clamp</sub> = 80% V<sub>CES</sub>, T<sub>J</sub> = 150 °C, R<sub>G</sub> = 10 Ω, V<sub>GE</sub> = 15 V.
3. Pulse width limited by maximum junction temperature and turn-off within RBSOA.

**Table 2. Thermal data**

Symbol	Parameter	Value			Unit
		D <sup>2</sup> PAK, TO-220	DPAK	TO-220FP	
R <sub>thJC</sub>	Thermal resistance, junction-to-case IGBT	1.9	2.0	5.1	°C/W
	Thermal resistance, junction-to-case diode	4	4.5	7	
R <sub>thJA</sub>	Thermal resistance, junction-to-ambient	62.5	100	62.5	°C/W

## 2 Electrical characteristics

$T_C = 25\text{ °C}$  unless otherwise specified

**Table 3. Static**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage	$V_{GE} = 0\text{ V}, I_C = 1\text{ mA}$	600			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}, I_C = 3\text{ A}$		2.2	2.75	V
		$V_{GE} = 15\text{ V}, I_C = 3\text{ A}, T_J = 125\text{ °C}$		1.8		
$V_{GE(th)}$	Gate threshold voltage	$V_{CE} = V_{GE}, I_C = 250\text{ }\mu\text{A}$	4.5		6.5	V
$I_{CES}$	Collector cut-off current	$V_{GE} = 0\text{ V}, V_{CE} = 600\text{ V}$			0.15	mA
		$V_{GE} = 0\text{ V}, V_{CE} = 600\text{ V}, T_J = 125\text{ °C}^{(1)}$			1	
$I_{GES}$	Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = \pm 20\text{ V}$			$\pm 100$	nA
$g_{fs}^{(2)}$	Forward transconductance	$V_{CE} = 15\text{ V}, I_C = 3\text{ A}$		1.9		S

1. Specified by design, not tested in production.

2. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%.

**Table 4. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{ies}$	Input capacitance	$V_{CE} = 25\text{ V}, f = 1\text{ MHz}, V_{GE} = 0\text{ V}$	-	380	-	pF
$C_{oes}$	Output capacitance		-	46	-	pF
$C_{res}$	Reverse transfer capacitance		-	8.5	-	pF
$Q_g$	Total gate charge	$V_{CC} = 390\text{ V}, I_C = 3\text{ A}, V_{GE} = 0\text{ to }15\text{ V}$ (see Figure 19. Gate charge test circuit)	-	19	-	nC
$Q_{ge}$	Gate-emitter charge		-	5	-	nC
$Q_{gc}$	Gate-collector charge		-	9	-	nC

**Table 5. Switching on/off (inductive load)**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{CC} = 390\text{ V}, I_C = 3\text{ A},$	-	17	-	ns
$t_r$	Current rise time	$R_G = 10\ \Omega, V_{GE} = 15\text{ V}$	-	6	-	ns
$(di/dt)_{on}$	Turn-on current slope	(see Figure 17. Test circuit for inductive load switching and Figure 20. Switching waveform)	-	655	-	A/ $\mu$ s
$t_{d(on)}$	Turn-on delay time	$V_{CC} = 390\text{ V}, I_C = 3\text{ A},$	-	16.5	-	ns
$t_r$	Current rise time	$R_G = 10\ \Omega, V_{GE} = 15\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	6.5	-	ns
$(di/dt)_{on}$	Turn-on current slope	(see Figure 17. Test circuit for inductive load switching and Figure 20. Switching waveform)	-	575	-	A/ $\mu$ s
$t_r(V_{off})$	Off voltage rise time	$V_{CC} = 390\text{ V}, I_C = 3\text{ A},$	-	33	-	ns
$t_{d(off)}$	Turn-off delay time	$R_G = 10\ \Omega, V_{GE} = 15\text{ V}$	-	72	-	ns
$t_f$	Current fall time	(see Figure 17. Test circuit for inductive load switching and Figure 20. Switching waveform)	-	82	-	ns
$t_r(V_{off})$	Off voltage rise time	$V_{CC} = 390\text{ V}, I_C = 3\text{ A},$	-	60	-	ns
$t_{d(off)}$	Turn-off delay time	$R_G = 10\ \Omega, V_{GE} = 15\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	106	-	ns
$t_f$	Current fall time	(see Figure 17. Test circuit for inductive load switching and Figure 20. Switching waveform)	-	136	-	ns

**Table 6. Switching energy (inductive load)**

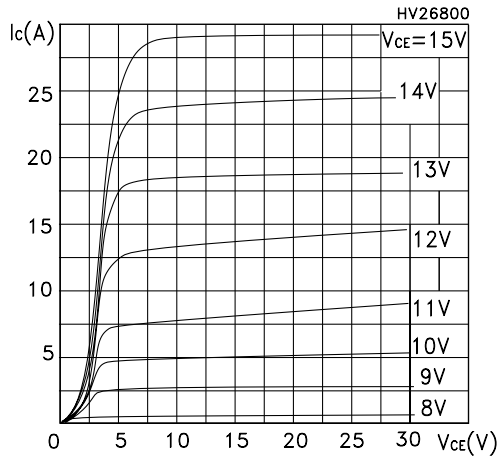
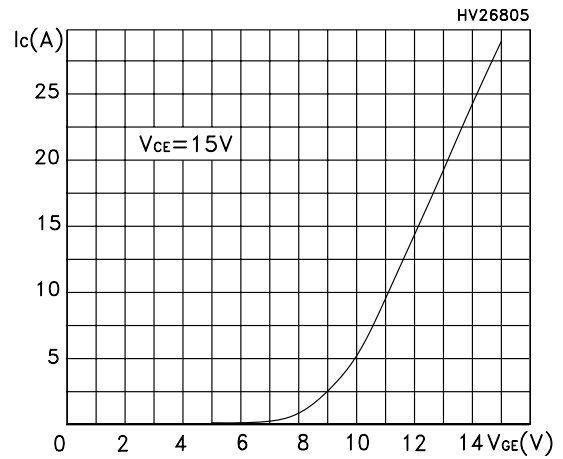
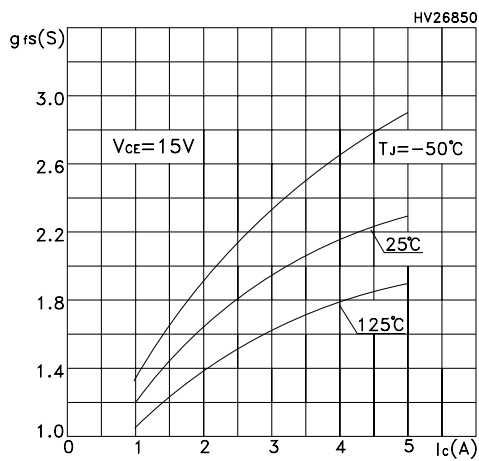
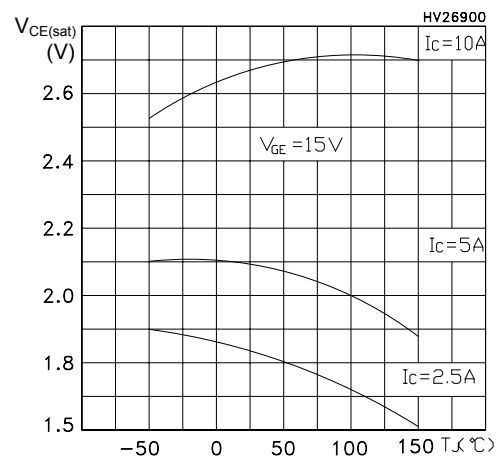
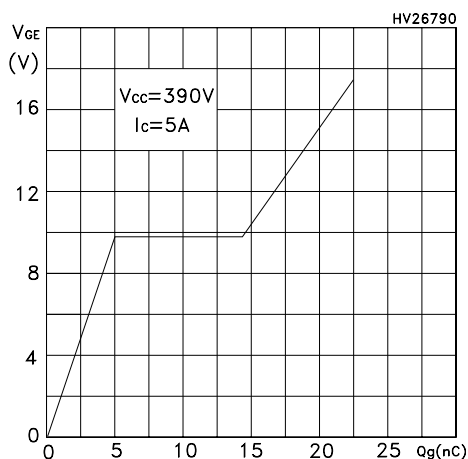
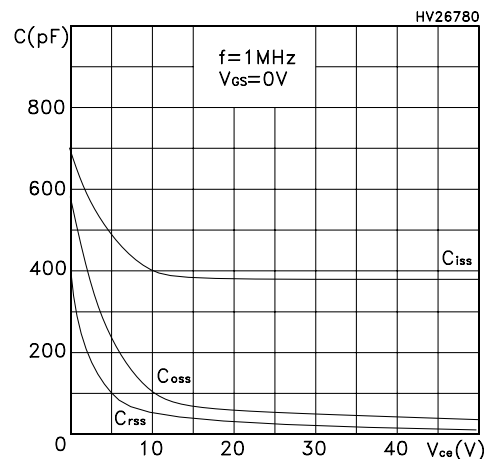
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$E_{on}^{(1)}$	Turn-on switching energy	$V_{CE} = 390\text{ V}, I_C = 3\text{ A},$	-	55	-	$\mu$ J
$E_{off}^{(2)}$	Turn-off switching energy	$R_G = 10\ \Omega, V_{GE} = 15\text{ V}$	-	85	-	$\mu$ J
$E_{ts}$	Total switching energy	(see Figure 17. Test circuit for inductive load switching)	-	140	-	$\mu$ J
$E_{on}^{(1)}$	Turn-on switching energy	$V_{CE} = 390\text{ V}, I_C = 3\text{ A},$	-	87	-	$\mu$ J
$E_{off}^{(2)}$	Turn-off switching energy	$R_G = 10\ \Omega, V_{GE} = 15\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	162	-	$\mu$ J
$E_{ts}$	Total switching energy	(see Figure 17. Test circuit for inductive load switching)	-	249	-	$\mu$ J

1. Including the reverse recovery of the diode.

2. Including the tail of the collector current.

**Table 7. Diode switching characteristics (inductive load)**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_F$	Forward on-voltage	$I_F = 3A$	-	1.6	2.1	V
		$I_F = 3A, T_J = 125^\circ C$	-	1.3		
$t_{rr}$	Reverse recovery time	$I_F = 3A, V_R = 30V, di/dt = 100A/\mu s$	-	23.5		ns
$Q_{rr}$	Reverse recovery charge	(see Figure 18. Diode reverse recovery waveform)	-	16.5		nC
$I_{rrm}$	Reverse recovery current		-	1.4		A
$t_{rr}$	Reverse recovery time	$I_F = 3A, V_R = 30V, di/dt = 100A/\mu s,$	-	39		ns
$Q_{rr}$	Reverse recovery charge	$T_J = 125^\circ C$ (see Figure 18. Diode reverse recovery waveform)	-	39		nC
$I_{rr}$	Reverse recovery current		-	2		A

**2.1 Electrical characteristics (curves)**
**Figure 1. Typical output characteristics**

**Figure 2. Typical transfer characteristics**

**Figure 3. Typical transconductance characteristics**

**Figure 4. Typical collector-emitter on voltage vs temperature**

**Figure 5. Typical gate charge characteristics**

**Figure 6. Typical capacitance characteristics**


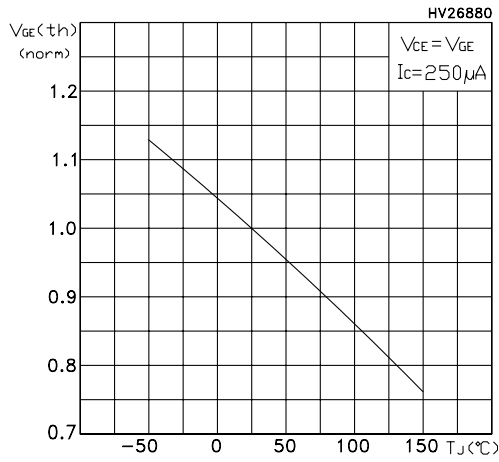
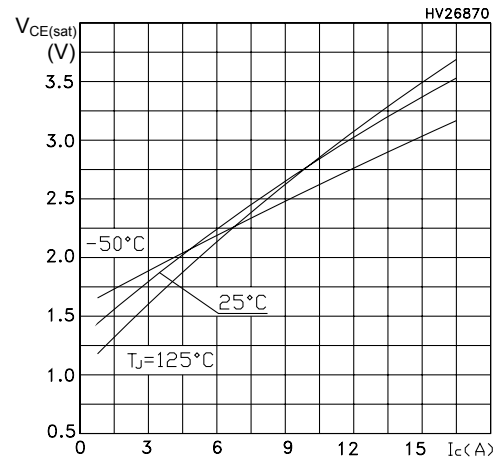
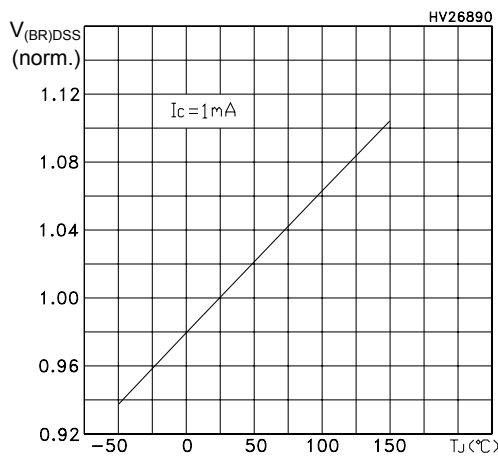
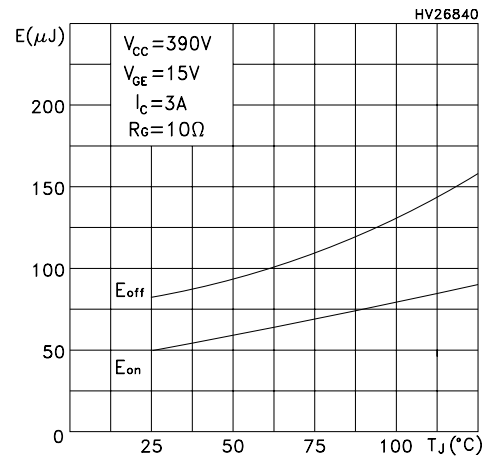
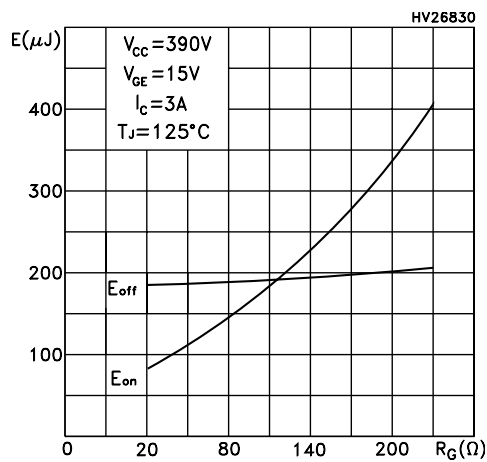
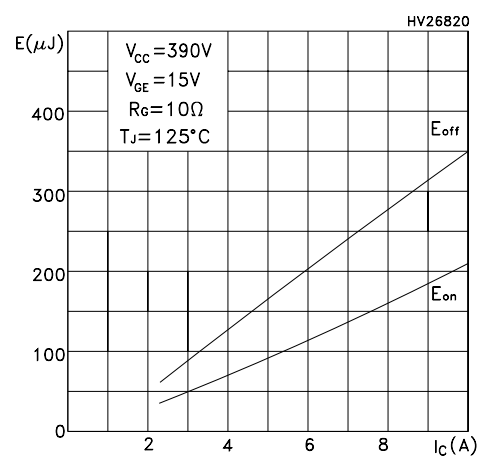
**Figure 7. Normalized gate threshold vs temperature**

**Figure 8. Typical collector-emitter on voltage vs collector current**

**Figure 9. Normalized breakdown voltage vs temperature**

**Figure 10. Typical switching energy vs temperature**

**Figure 11. Typical switching energy vs gate resistance**

**Figure 12. Typical switching energy vs collector current**


Figure 13. Reverse bias safe operating area

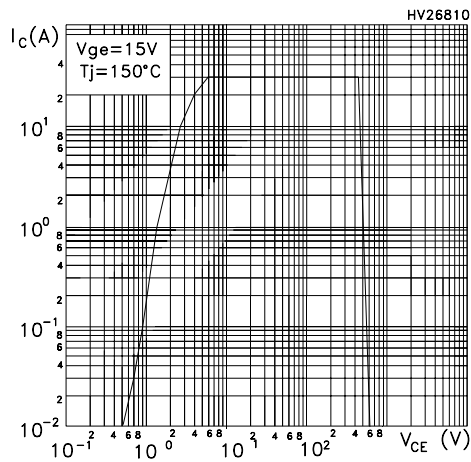


Figure 14. Normalized transient thermal impedance for D<sup>2</sup>PAK, DPAK and TO-220

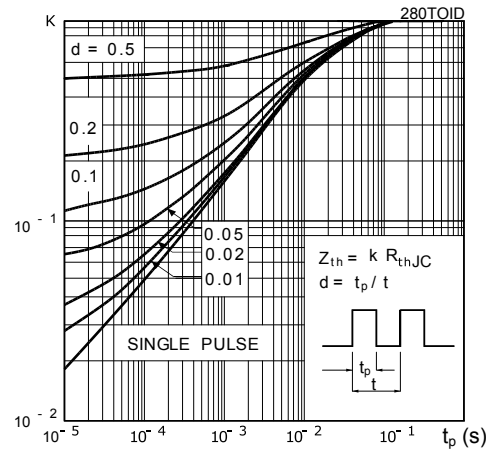


Figure 15. Normalized transient thermal impedance for TO-220FP

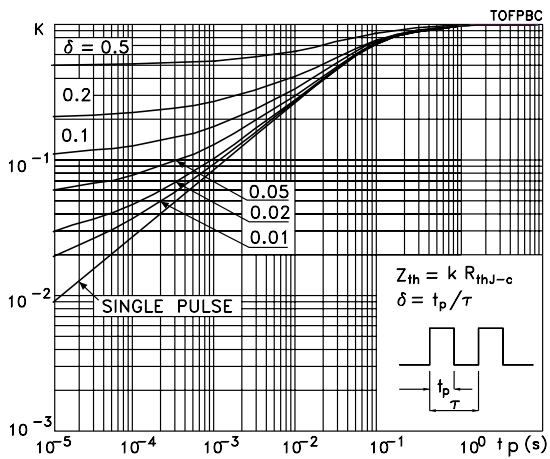
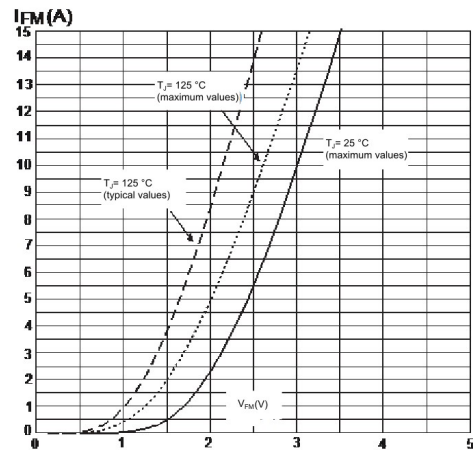


Figure 16. Typical emitter-collector diode characteristics





### 3 Test circuits

Figure 17. Test circuit for inductive load switching

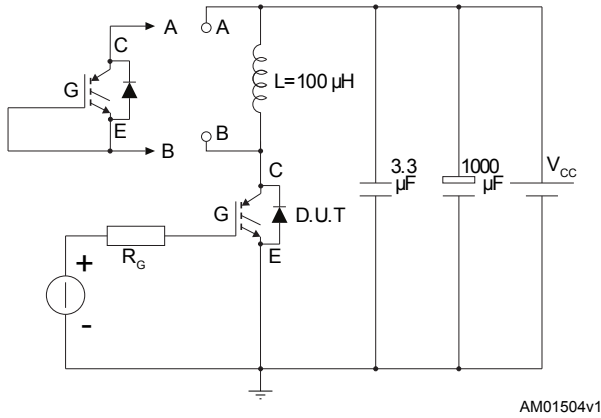


Figure 18. Diode reverse recovery waveform

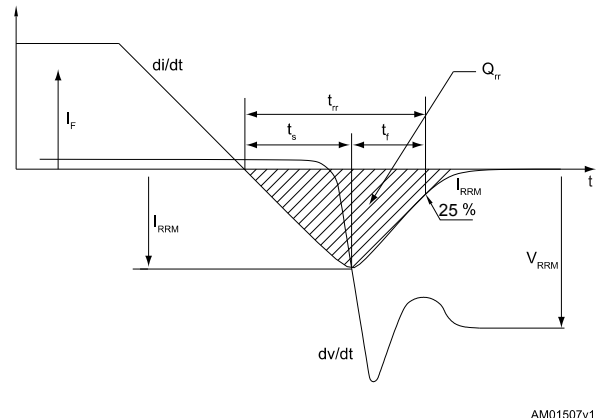


Figure 19. Gate charge test circuit

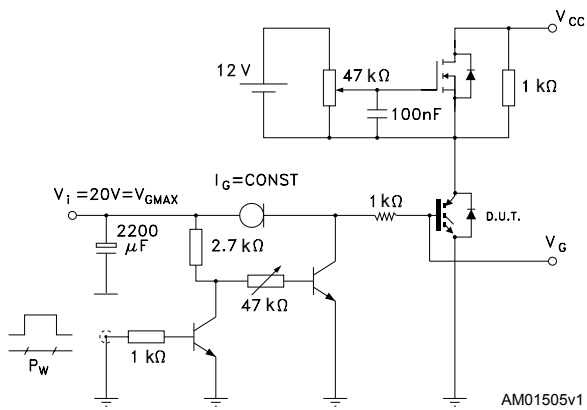
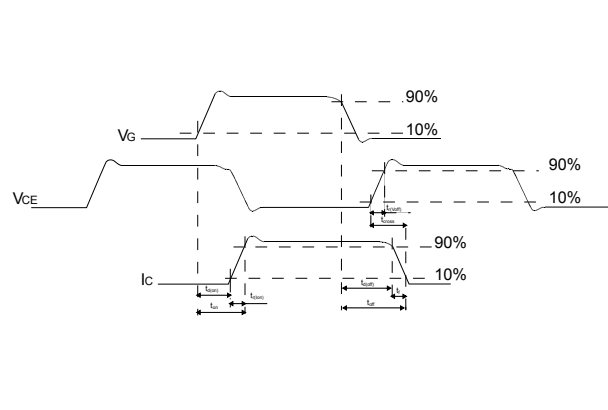


Figure 20. Switching waveform

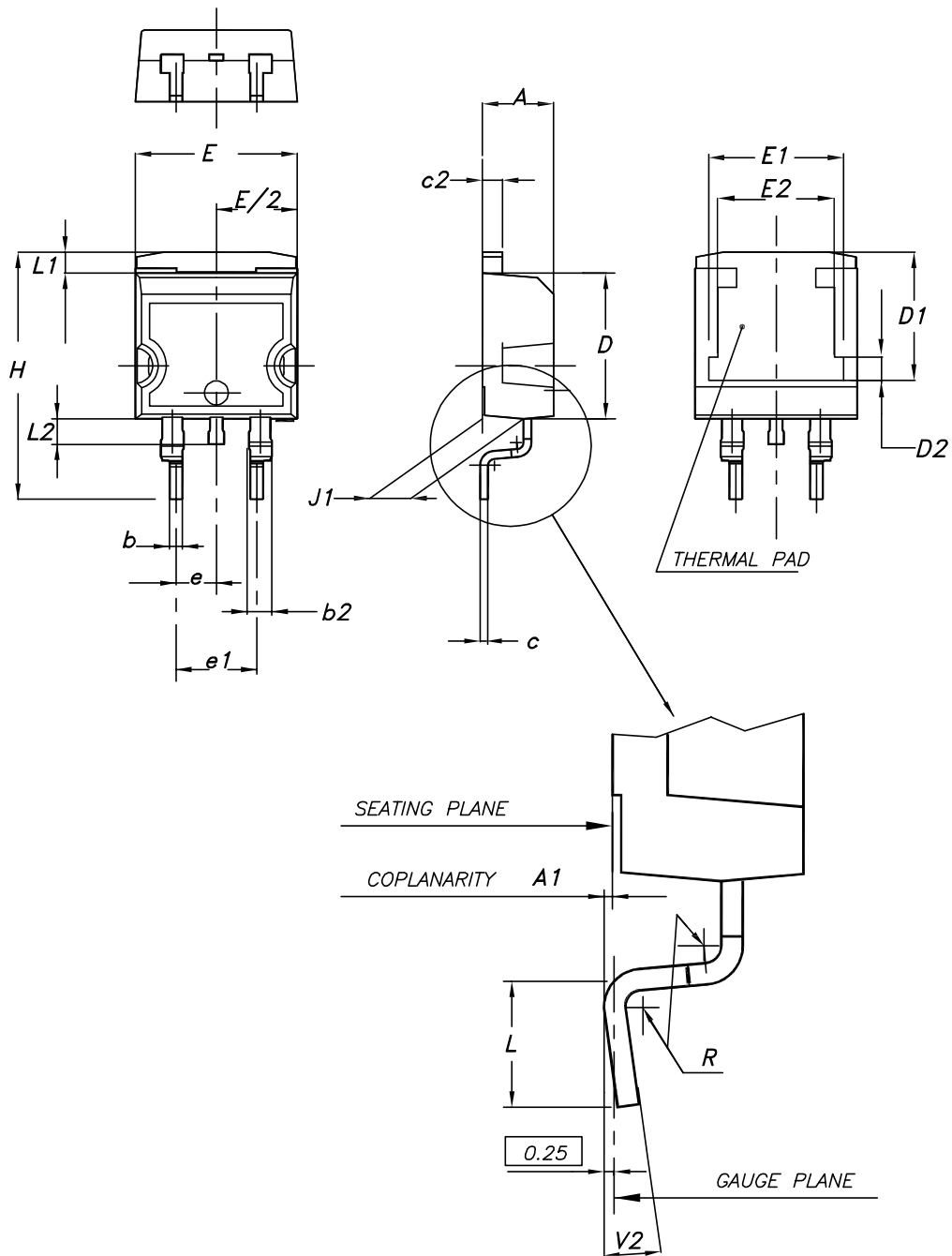


## 4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

### 4.1 D<sup>2</sup>PAK (TO-263) package information

Figure 21. D<sup>2</sup>PAK (TO-263) type A package outline

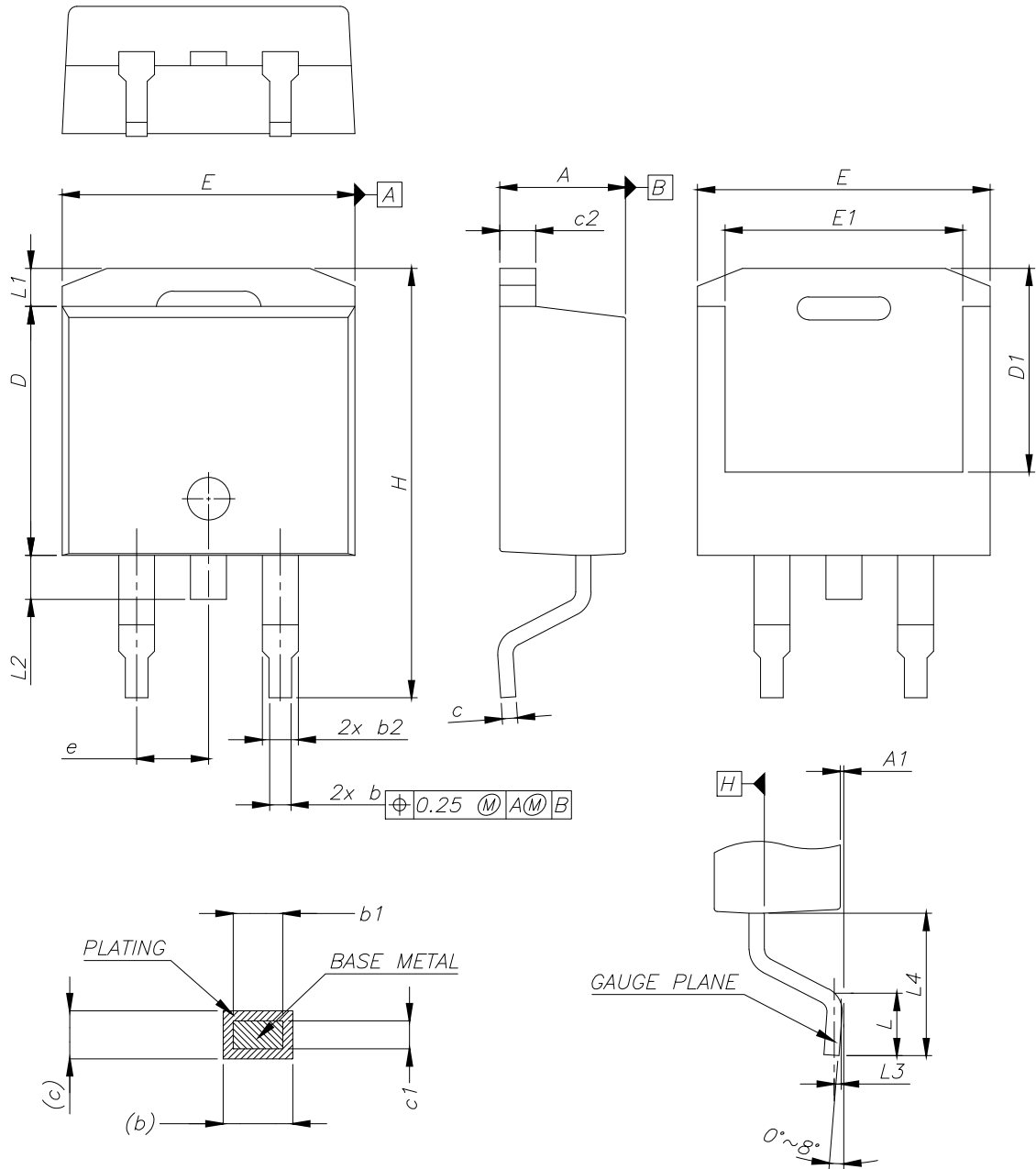


0079457\_26

**Table 8. D<sup>2</sup>PAK (TO-263) type A package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50	7.75	8.00
D2	1.10	1.30	1.50
E	10.00		10.40
E1	8.30	8.50	8.70
E2	6.85	7.05	7.25
e		2.54	
e1	4.88		5.28
H	15.00		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.40	
V2	0°		8°

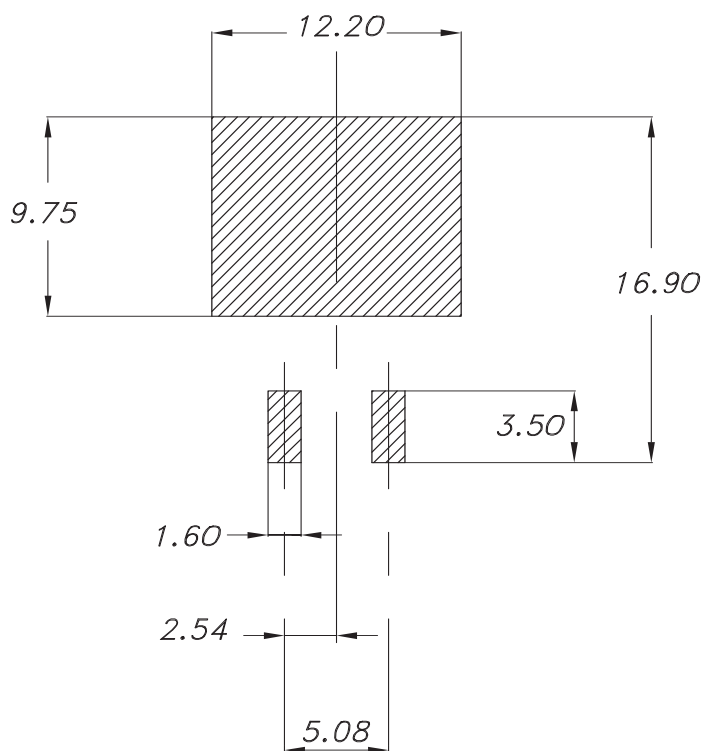
Figure 22. D<sup>2</sup>PAK (TO-263) type B package outline



0079457\_26\_B

**Table 9. D<sup>2</sup>PAK (TO-263) type B mechanical data**

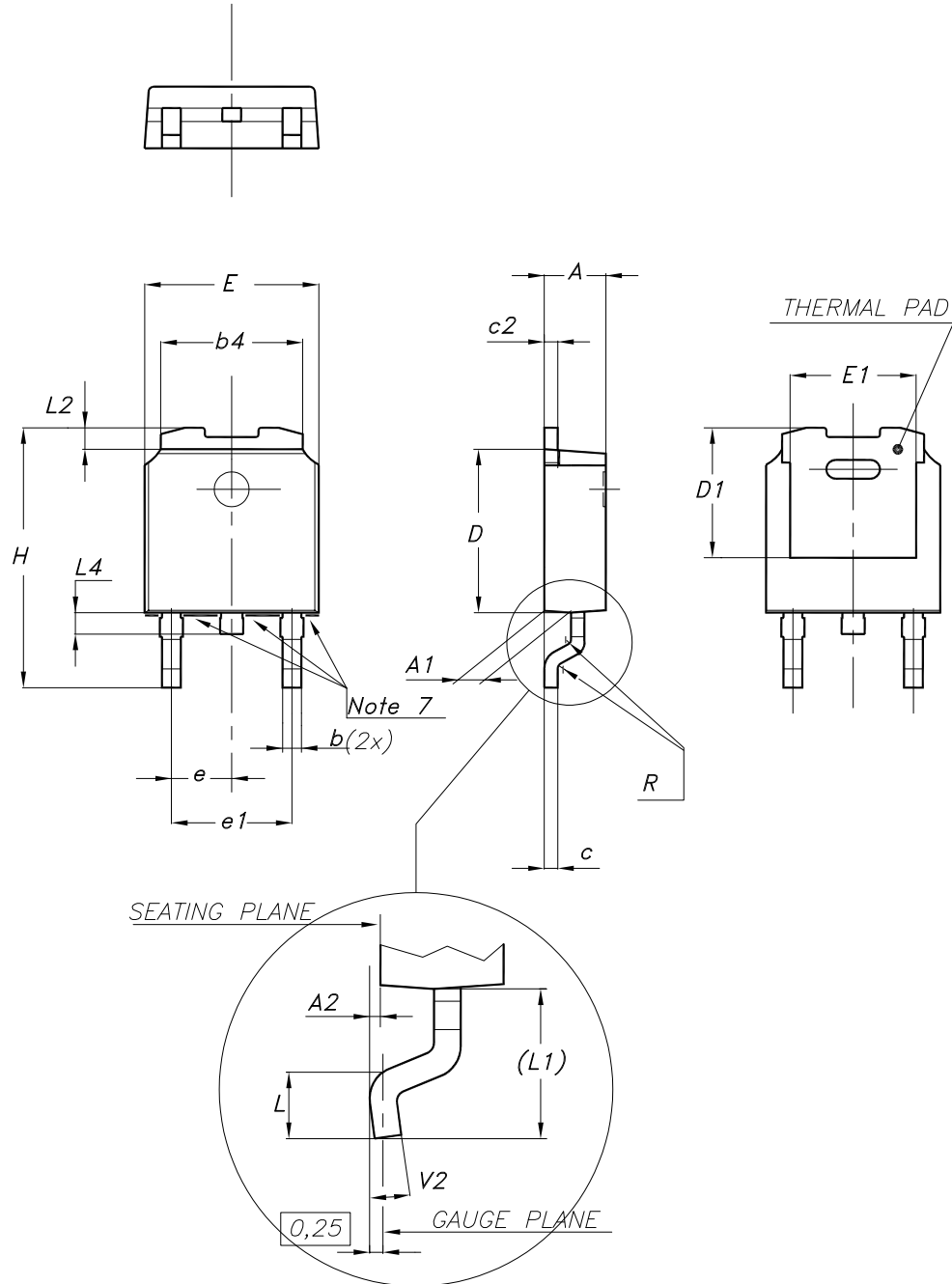
Dim.	mm		
	Min.	Typ.	Max.
A	4.36		4.56
A1	0		0.25
b	0.70		0.90
b1	0.51		0.89
b2	1.17		1.37
c	0.38		0.694
c1	0.38		0.534
c2	1.19		1.34
D	8.60		9.00
D1	6.90		7.50
E	10.15		10.55
E1	8.10		8.70
e	2.54 BSC		
H	15.00		15.60
L	1.90		2.50
L1			1.65
L2			1.78
L3		0.25	
L4	4.78		5.28

**Figure 23. D<sup>2</sup>PAK (TO-263) recommended footprint (dimensions are in mm)**


0079457\_Rev26\_footprint

4.2 DPAK (TO-252) type A package information

Figure 24. DPAK (TO-252) type A package outline



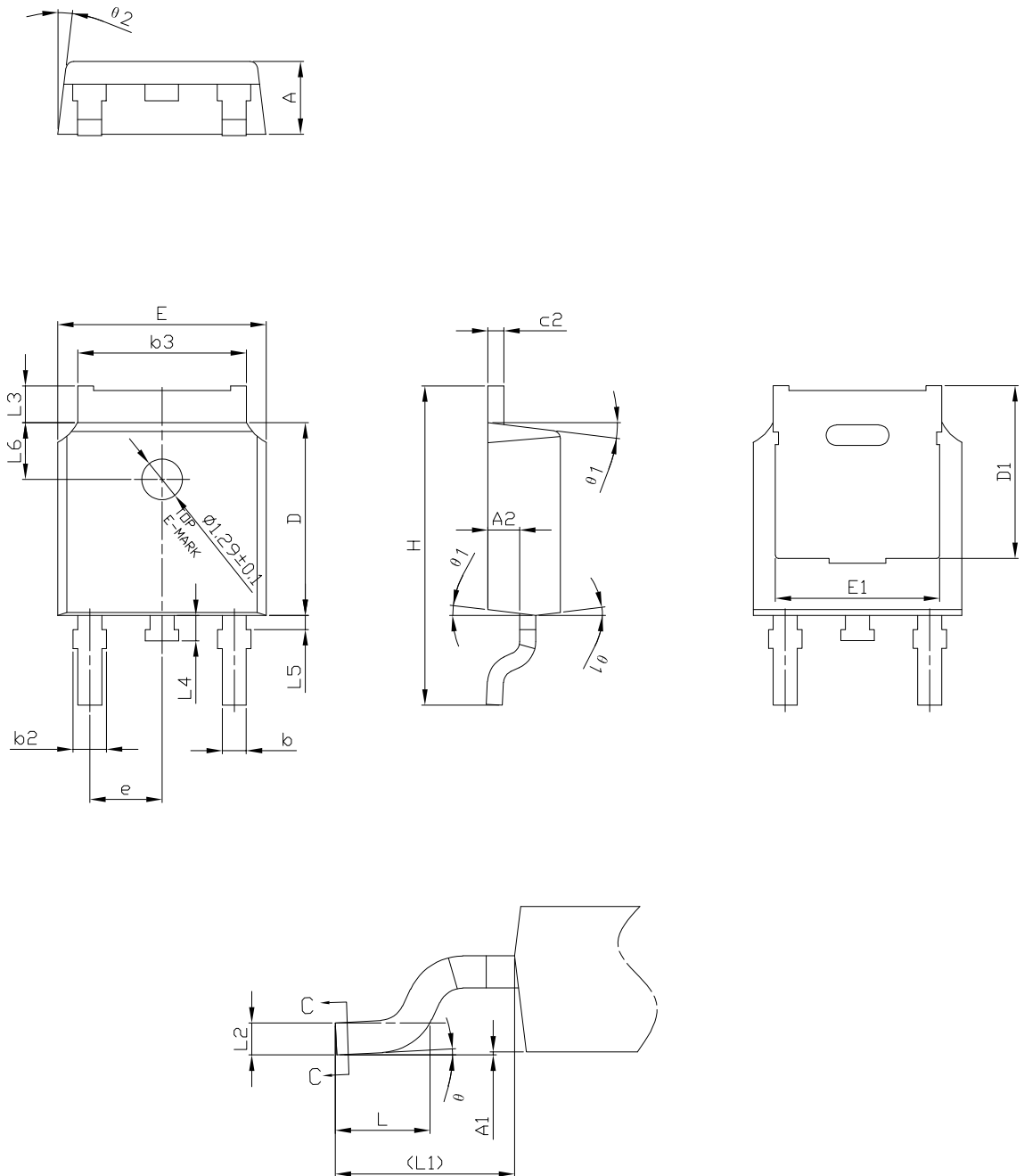
0068772\_A\_34

**Table 10. DPAK (TO-252) type A mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1	4.95	5.10	5.25
E	6.40		6.60
E1	4.60	4.70	4.80
e	2.159	2.286	2.413
e1	4.445	4.572	4.699
H	9.35		10.10
L	1.00		1.50
(L1)	2.60	2.80	3.00
L2	0.65	0.80	0.95
L4	0.60		1.00
R		0.20	
V2	0°		8°

### 4.3 DPAK (TO-252) type C3 package information

Figure 25. DPAK (TO-252) type C3 package outline



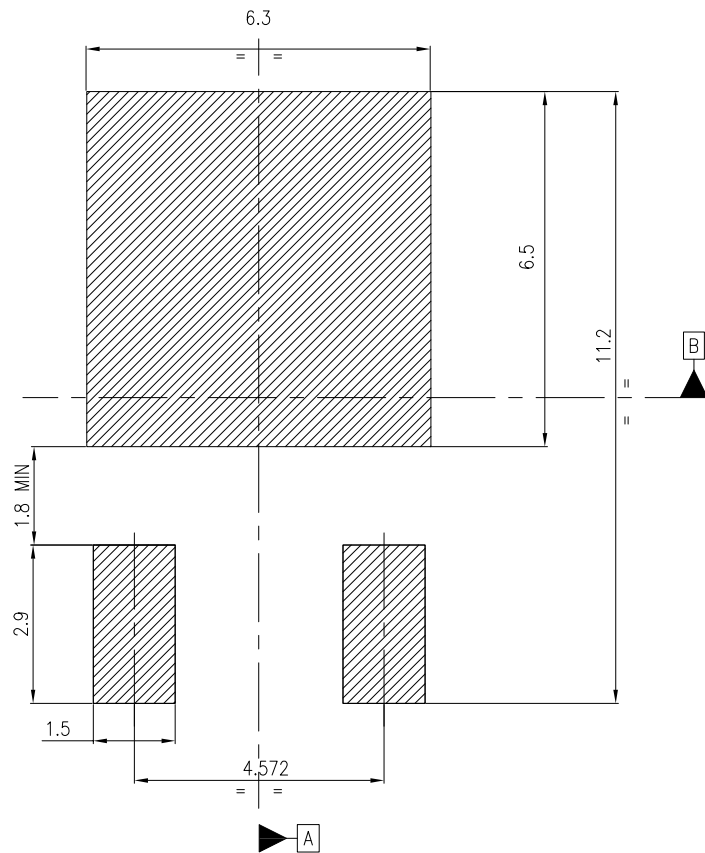
0068772\_type-C3\_rev34



**Table 11. DPAK (TO-252) type C3 mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	2.20	2.30	2.38
A1	0.00		0.10
A2	0.90	1.01	1.10
b	0.72		0.85
b2	0.72		1.10
b3	5.13	5.33	5.46
c	0.47		0.60
c2	0.47		0.60
D	6.00	6.10	6.20
D1	5.20	5.45	5.70
E	6.50	6.60	6.70
E1	5.00	5.20	5.40
e	2.186	2.286	2.386
H	9.80	10.10	10.40
L	1.40	1.50	1.70
L1	2.90 REF		
L2	0.51 BSC		
L3	0.90		1.25
L4	0.60	0.80	1.00
L5	0.15		0.75
L6	1.80 REF		
$\theta$	0°		8°
$\theta 1$	5°	7°	9°
$\theta 2$	5°	7°	9°

Figure 26. DPAK (TO-252) recommended footprint (dimensions are in mm)



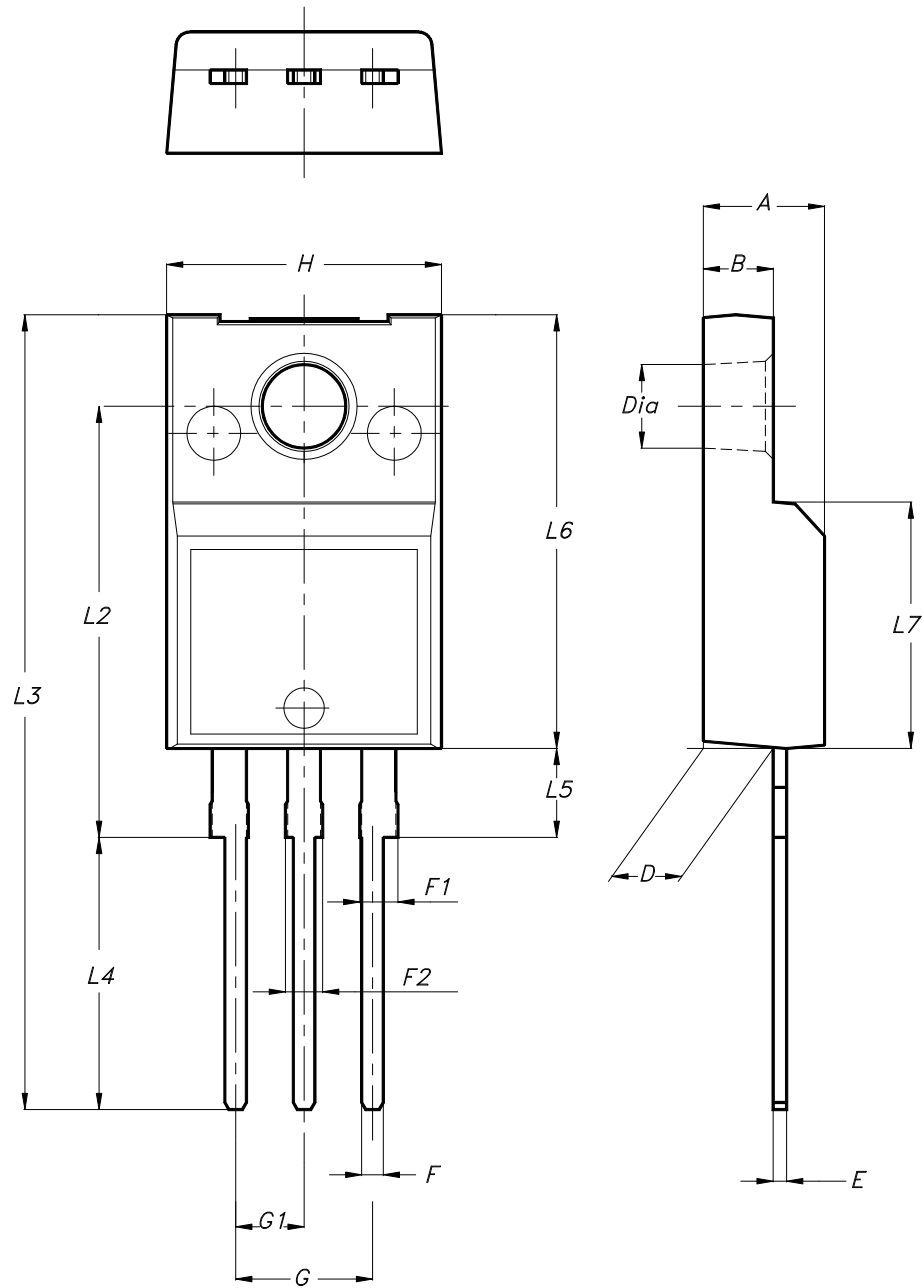
Notes:

- 1) This footprint is able to ensure insulation up to 630 Vrms (according to CEI IEC 664-1)
- 2) The device must be positioned within  $\boxed{\oplus 0.05 \text{ A B}}$

FP\_0068772\_34

#### 4.4 TO-220FP type B package information

Figure 27. TO-220FP type B package outline



7012510\_B\_rev.14

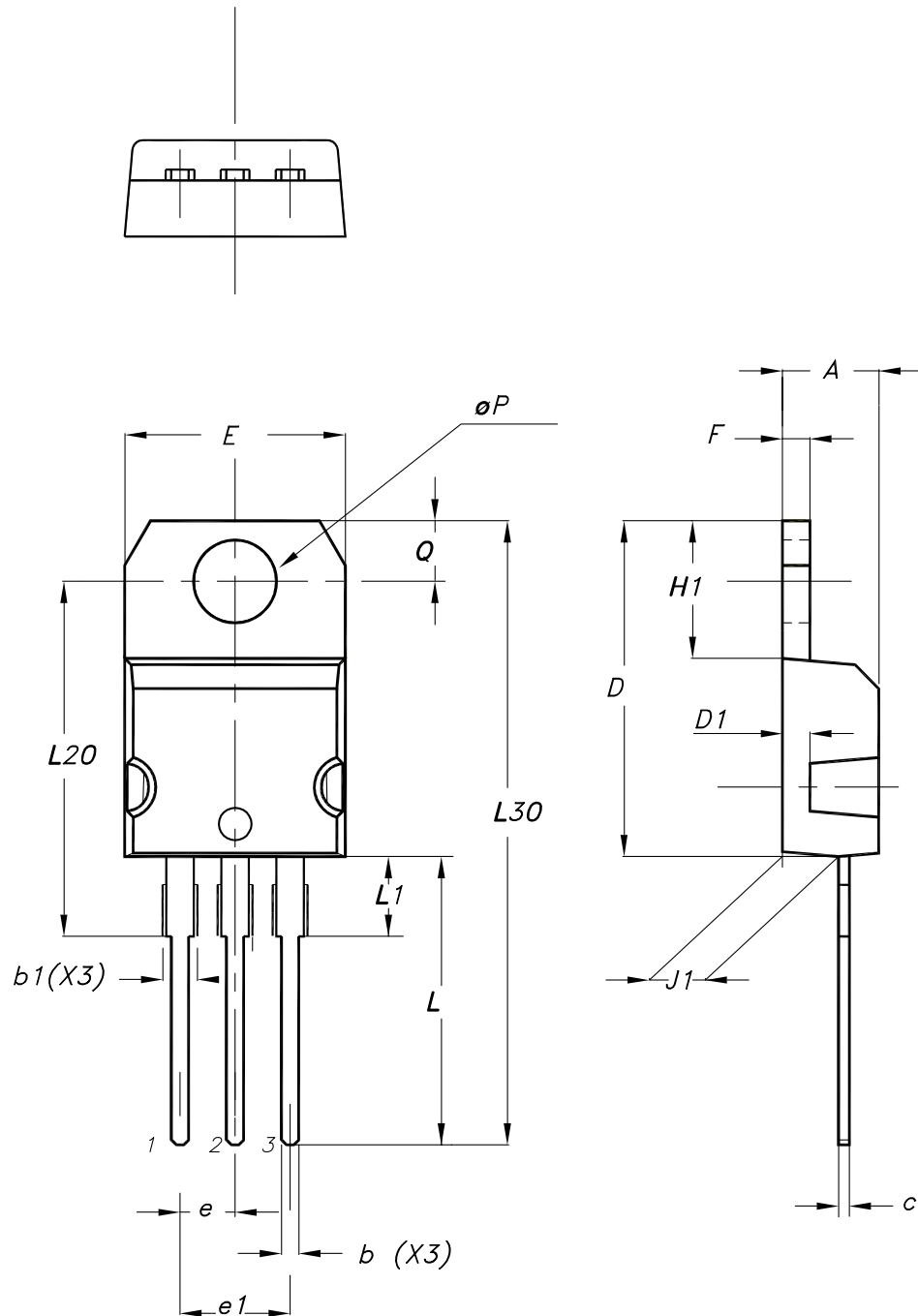


Table 12. TO-220FP type B package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
B	2.50		2.70
D	2.50		2.75
E	0.45		0.70
F	0.75		1.00
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.20
G1	2.40		2.70
H	10.00		10.40
L2		16.00	
L3	28.60		30.60
L4	9.80		10.60
L5	2.90		3.60
L6	15.90		16.40
L7	9.00		9.30
Dia	3.00		3.20

### 4.5 TO-220 type A package information

Figure 28. TO-220 type A package outline



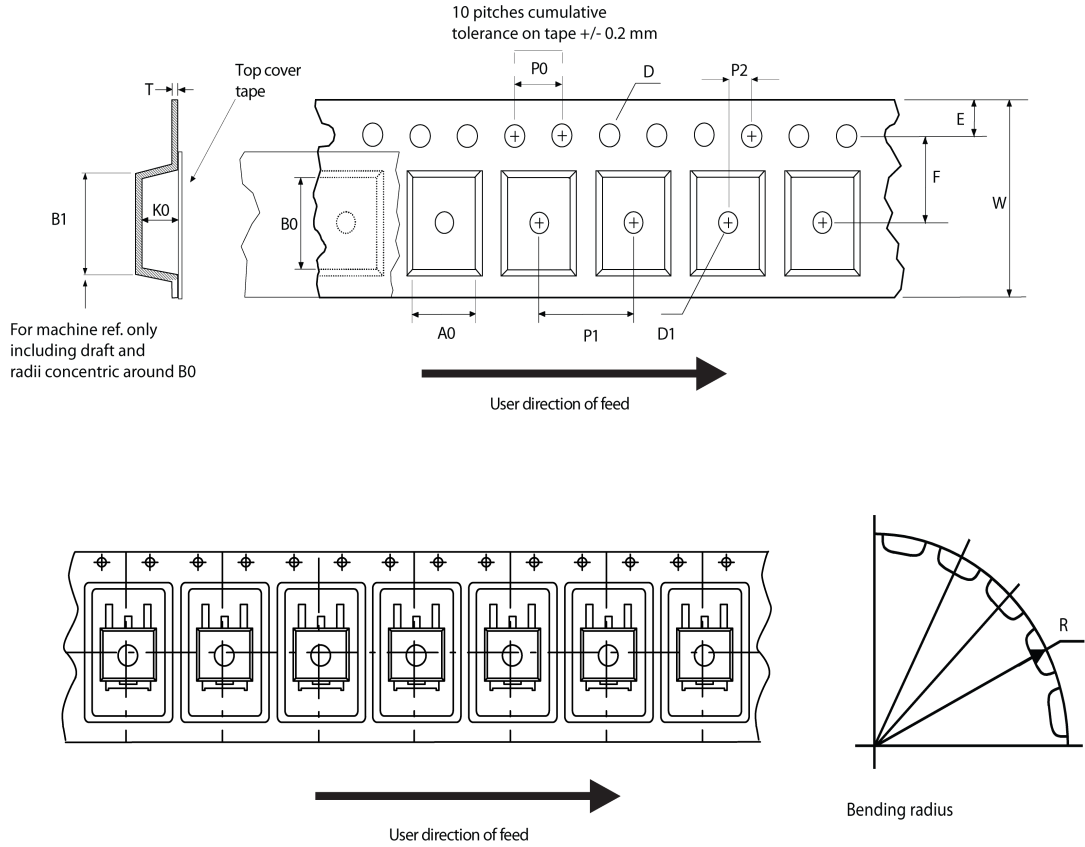
0015988\_typeA\_Rev\_23

**Table 13. TO-220 type A package mechanical data**

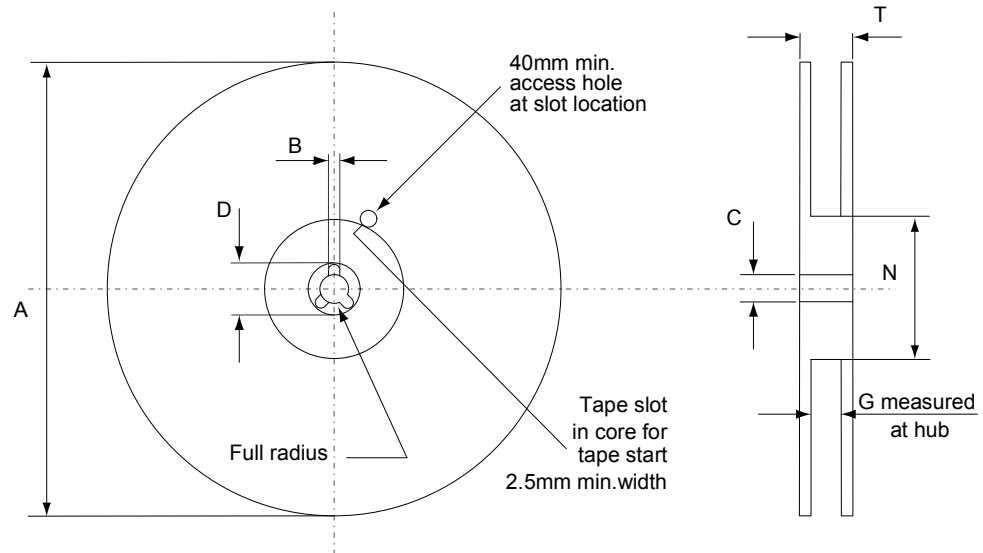
Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.55
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10.00		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13.00		14.00
L1	3.50		3.93
L20		16.40	
L30		28.90	
øP	3.75		3.85
Q	2.65		2.95
Slug flatness		0.03	0.10

### 4.6 D<sup>2</sup>PAK type A packing information

Figure 29. D<sup>2</sup>PAK tape outline



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**Figure 30. D<sup>2</sup>PAK reel outline**


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**Table 14. D<sup>2</sup>PAK tape and reel mechanical data**

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base quantity		1000
P2	1.9	2.1	Bulk quantity		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			



## 4.7 D<sup>2</sup>PAK type B packing information

Figure 31. D<sup>2</sup>PAK type B tape outline

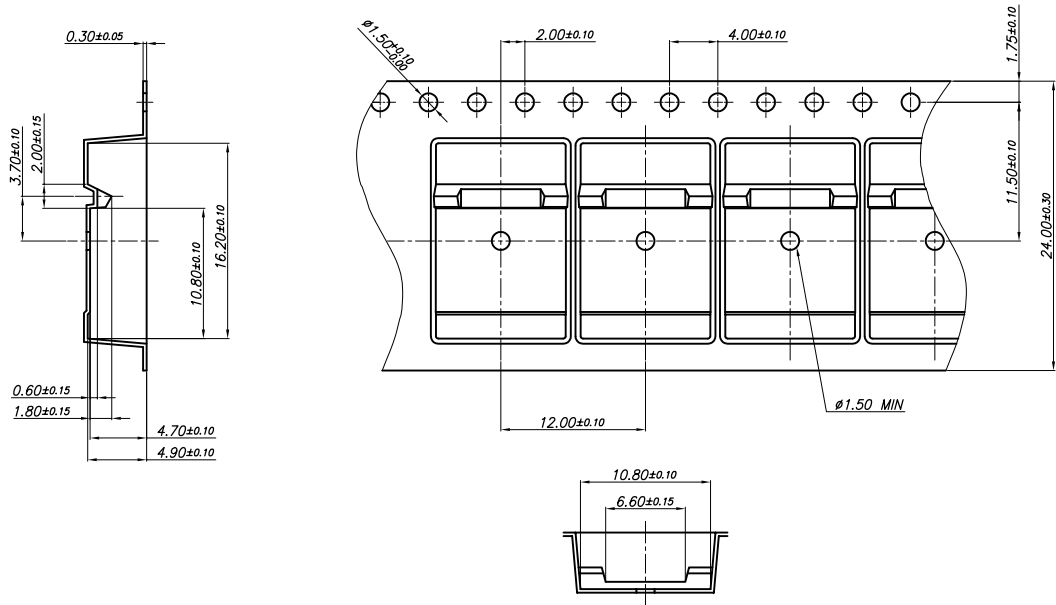
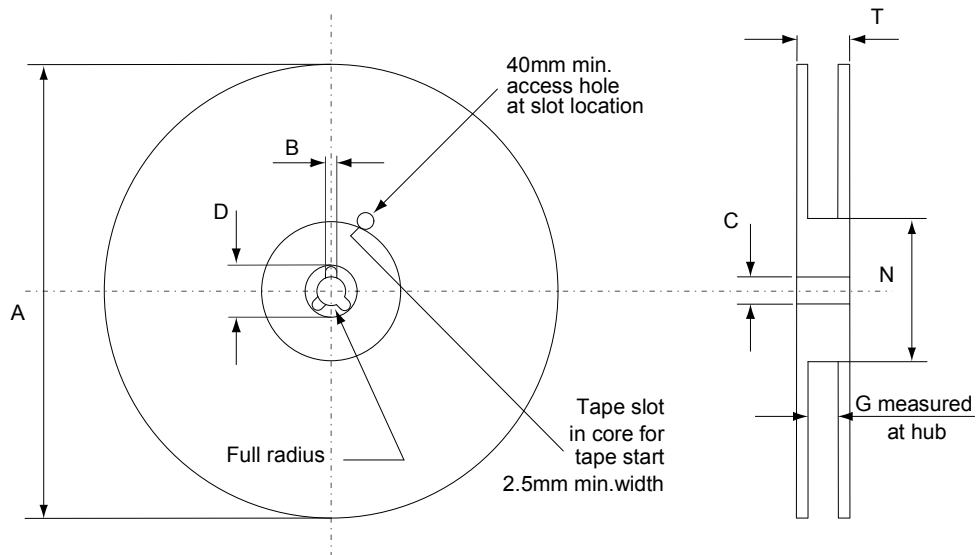


Figure 32. D<sup>2</sup>PAK type B reel outline



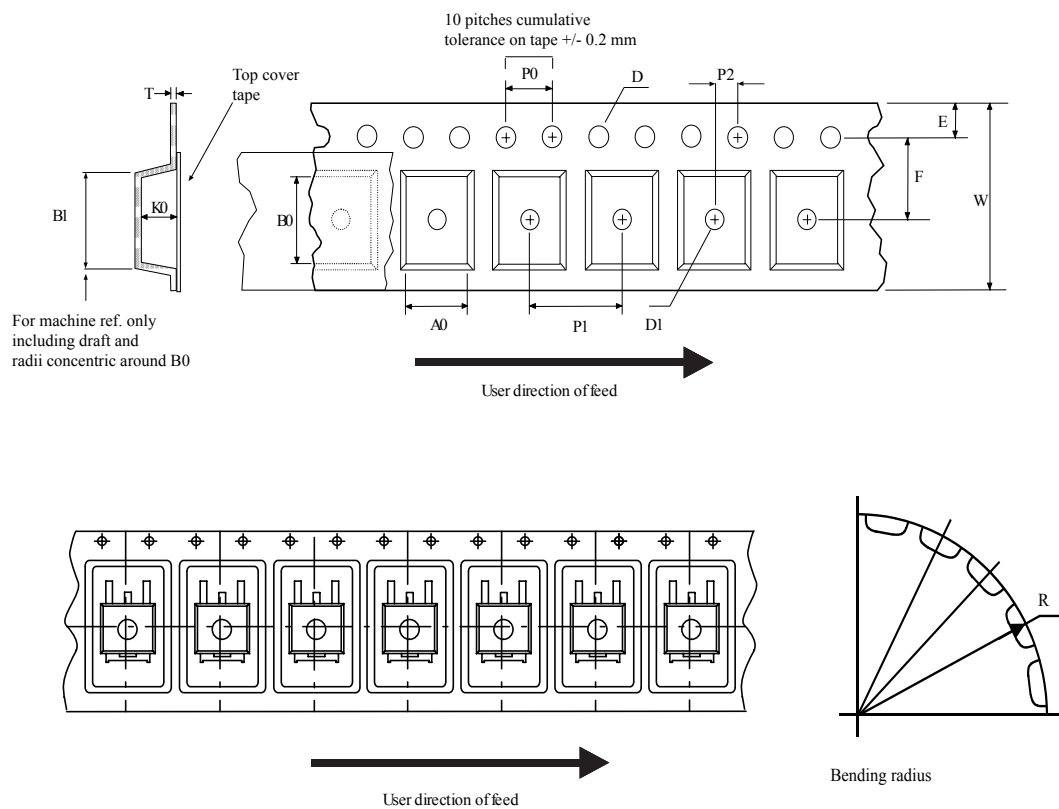
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Table 15. D<sup>2</sup>PAK type B reel mechanical data

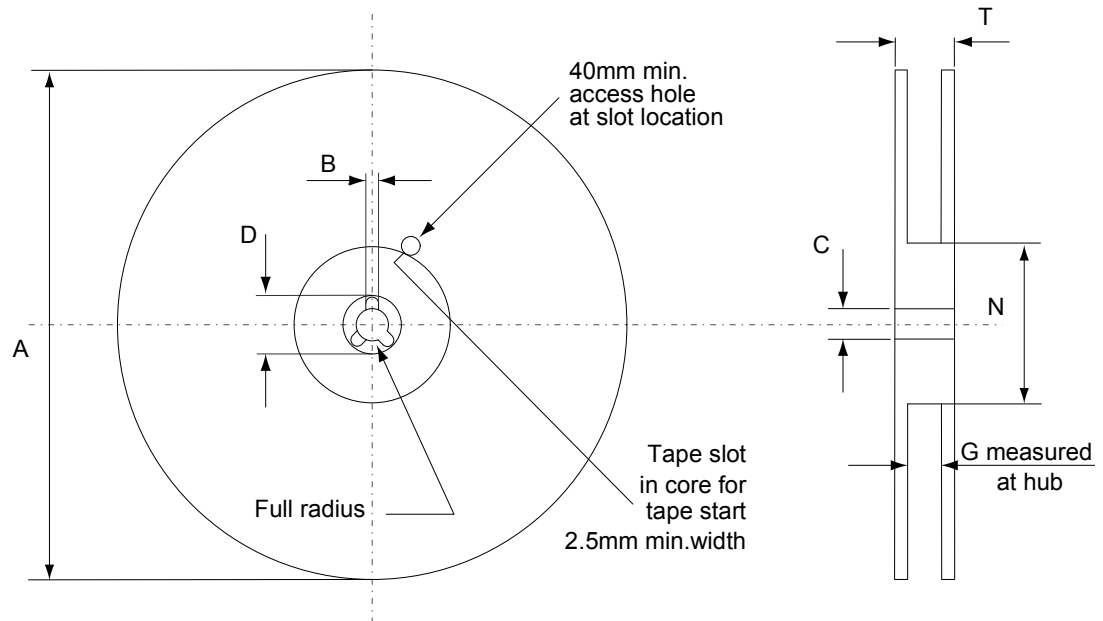
Dim.	mm	
	Min.	Max.
A		330
B	1.5	
C	12.8	13.2
D	20.2	
G	24.4	26.4
N	100	
T		30.4

### 4.8 DPAK (TO-252) packing information

Figure 33. DPAK (TO-252) tape outline



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**Figure 34. DPAK (TO-252) reel outline**


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**Table 16. DPAK (TO-252) tape and reel mechanical data**

Dim.	Tape		Dim.	Reel	
	mm			mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			



## 5 Ordering information

Table 17. Order codes

Order codes	Marking	Package	Packing
STGB8NC60KD	GB8NC60KD	D <sup>2</sup> PAK	Tape and reel
STGD8NC60KD	GD8NC60KD	DPAK	
STGF8NC60KD	GF8NC60KD	TO-220FP	Tube
STGP8NC60KD	GP8NC60KD	TO-220	



## Revision history

**Table 18. Document revision history**

Date	Revision	Changes
02-Oct-2007	1	First release.
01-Apr-2008	2	Updated <i>Figure 14</i> and <i>Figure 17</i>
09-Jun-2023	3	Updated the entire <a href="#">Section 4 Package information</a> . Minor text changes.



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